

**VSP-MIKRON**

RoHS

 $V_{RRM}=1200V$ $I_F = 60A$ **Diode-Die****KD60120FU**

Die Size-8.7 x 5.0мм.

Ultra low losses
Passivation : Silicon Oxide

предварительная для опытных образцов

Maximum rated values

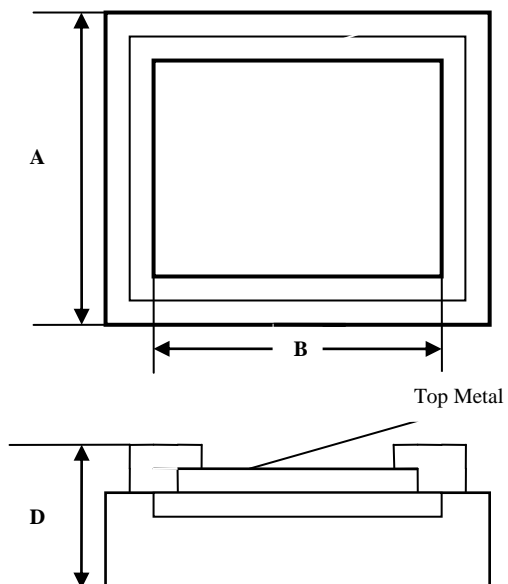
Parameter	Symbol	Unit	min	max
Repetitive peak reverse voltage	V_{RRM}	V	-	1200
Continuous forward current	I_F	A	-	60
Repetitive peak forward current*	I_{FRM}	A	-	100
Junction temperature	T_{vj}	°C	-	150

*Limited by $T_{vj\ max}$ **Diode Characteristics values**

Parameter	Symbol	Conditions	min	typ	max	Unit
Continuous forward voltage	V_F	$I_F=60A, T_{vj}= 25^\circ C$		2.3	2,4	V
Continuous reverse current	I_R	$V_R=1200V$ $\frac{T_{vj}= 25^\circ C}{T_{vj}= 125^\circ C}$		2	100	uA mA
Peak reverse recovery current	I_{RRM}	$I_F=50A, V_R=700V,$ $di_F/dt=200A/uS,$ $T_{vj}= 25^\circ C$		уточняется		A
Recovered charge	Q_{rr}			уточняется		μC
Reverse Recovery Time	t_{rr}			уточняется		nS
Reverse Recovery Time	t_{rr}	$I_F=1A, V_R=30V,$ $di_F/dt=200A/uS.$		90	100	nS

Mechanical properties*Top metal: Al-* for Wire Bonding.*Backside metal: Ti-Ni-Ag* – for Soldering.

DIM	ITEM	μm
A_x A_y	Die Size	8700 5000
D	Thickness	350max.
Scribe line Width		60



www.vsp-mikron.com

физ.съем 550 кристаллов МЗУ-80%- 440 кристалла ВВ-95 плановый съем -418 кристаллов с пластины.